

# Medium power transistor (30V, 1.0A)

## 2SC5730

### ●Features

- 1) High speed switching. ( $T_f$  : Typ. : 35ns at  $I_c = 1.0A$ )
- 2) Low saturation voltage, typically  
(Typ. : 150mV at  $I_c = 500mA$ ,  $I_B = 50mA$ )
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SA2048

### ●Applications

Small signal low frequency amplifier  
High speed switching

### ●Structure

NPN Silicon epitaxial planar transistor

### ●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
2SC5730		○

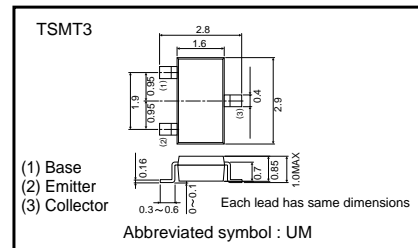
### ●Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CB0}$	30	V
Collector-emitter voltage	$V_{CE0}$	30	V
Emitter-base voltage	$V_{EB0}$	6	V
Collector current	$I_c$	1	A
	$I_{cP}$	2	A <sup>*1</sup>
Power dissipation	$P_c$	500	mW <sup>*2</sup>
Junction temperature	$T_j$	150	°C
Range of storage temperature	$T_{stg}$	-55~+150	°C

\*1  $P_w=10ms$

\*2 Each terminal mounted on a recommended land.

### ●External dimensions (Units : mm)



Transistor

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	30	–	–	V	I <sub>C</sub> =100μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	30	–	–	V	I <sub>C</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EBO</sub>	6	–	–	V	I <sub>E</sub> =100μA
Collector cut-off current	I <sub>CB0</sub>	–	–	1.0	μA	V <sub>CB</sub> =20V
Emitter cut-off current	I <sub>EBO</sub>	–	–	1.0	μA	V <sub>EB</sub> =4V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	–	150	300	mV	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA
DC current gain	h <sub>FE</sub>	120	–	390	–	V <sub>CE</sub> =2V, I <sub>C</sub> =100mA
Transition frequency	f <sub>T</sub>	–	270	–	MHz	V <sub>CE</sub> =10V, I <sub>E</sub> =–100mA, f=10MHz*1
Collector output capacitance	C <sub>ob</sub>	–	10	–	pF	V <sub>CB</sub> =10V, I <sub>E</sub> =0mA,*2 f=1MHz
Turn-on time	T <sub>on</sub>	–	30	–	ns	I <sub>C</sub> =1A,
Storage time	T <sub>stg</sub>	–	120	–	ns	I <sub>B1</sub> =0.1A
Fall time	T <sub>f</sub>	–	35	–	ns	I <sub>B2</sub> =–0.1A V <sub>CC</sub> ≈25V

\*1 Non repetitive pulse

\*2 See switching characteristics measurement circuits

●h<sub>FE</sub> RANK

Q	R
120-270	180-390

●Electrical characteristic curves

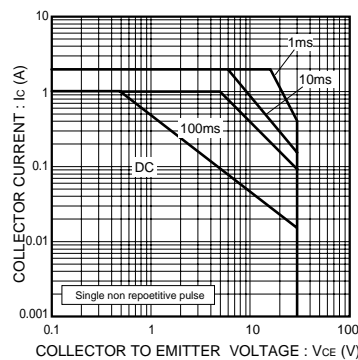


Fig.1 Safe operating area

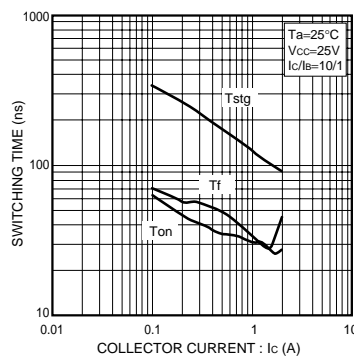


Fig.2 Switching Time

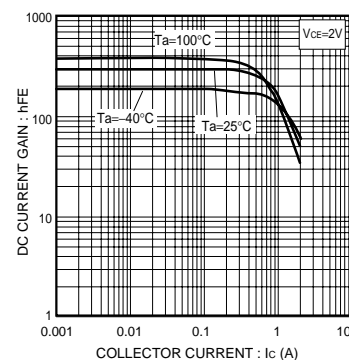


Fig.3 DC current gain vs. collector current

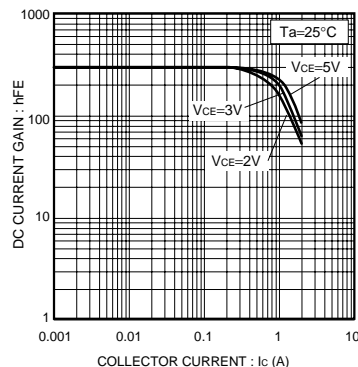


Fig.4 DC current gain vs. collector current

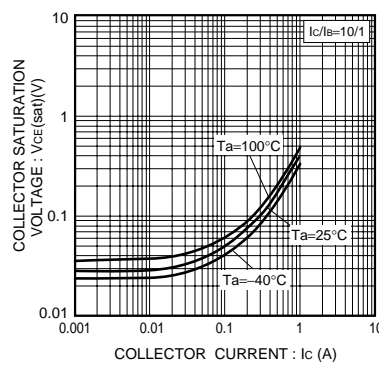


Fig.5 Collector-emitter saturation voltage vs. collector current

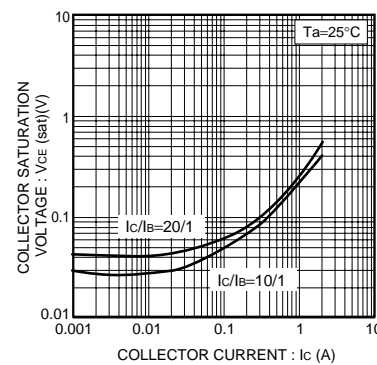


Fig.6 Collector-emitter saturation voltage vs. collector current

Transistor

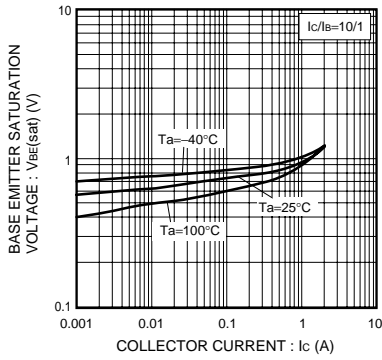


Fig.7 Base-emitter saturation voltage vs. collector current

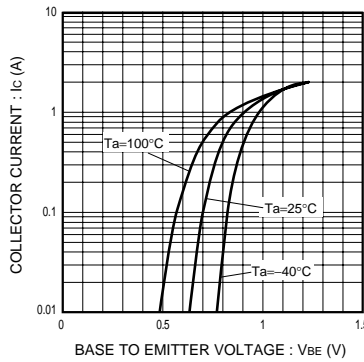


Fig.8 Ground emitter propagation characteristics

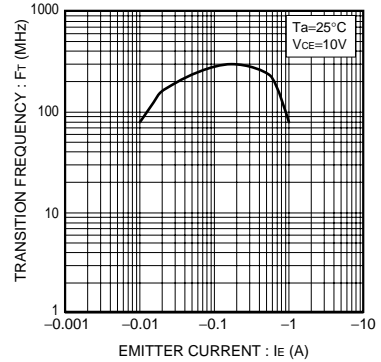


Fig.9 Transition frequency

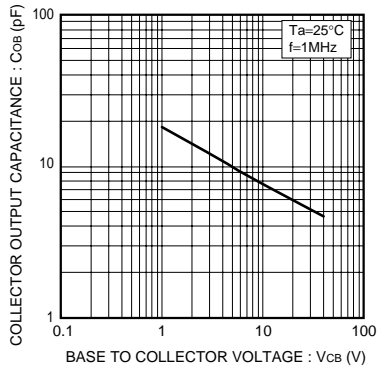
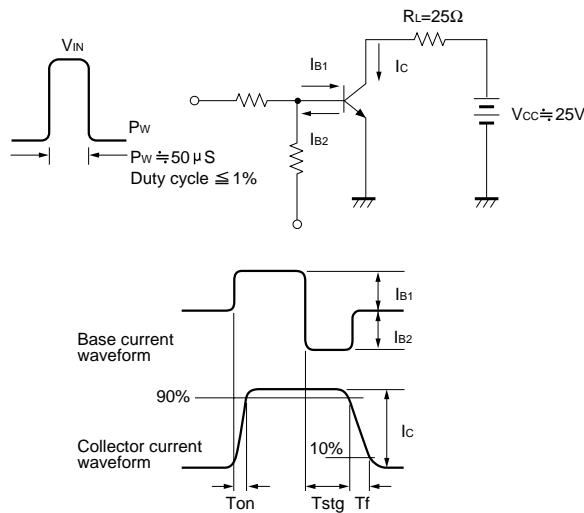


Fig.10 Collector output capacitance

●Switching characteristics measurement circuits



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